



PUMD18

50 V, 100 mA NPN/PNP resistor-equipped double transistor;
R1 = 4.7 k Ω , R2 = 10 k Ω

12 May 2023

Product data sheet

1. General description

NPN/PNP double Resistor-Equipped Transistor (RET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: PUMH18

PNP/PNP complement: PUMB18

2. Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplified circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

3. Applications

- Low current peripheral driver
- Controlling IC inputs
- Replacement of general purpose transistors in digital applications

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per transistor							
V _{CEO}	collector-emitter voltage	open base	[1]	-	-	50	V
I _O	output current		[1]	-	-	100	mA
R1	bias resistor 1 (input)		[2]	3.3	4.7	6.1	k Ω
R2/R1	bias resistor ratio		[2]	1.7	2.1	2.6	

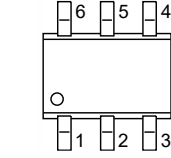
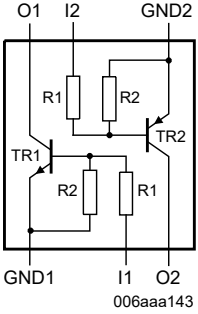
[1] For the PNP transistor with negative polarity.

[2] See section "Test information" for resistor calculation and test conditions.

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 kΩ, R2 = 10 kΩ

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1	 <p>TSSOP6 (SOT363)</p>	
2	I1	input (base) TR1		
3	O2	output (collector) TR2		
4	GND2	GND (emitter) TR2		
5	I2	input (base) TR2		
6	O1	output (collector) TR1		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PUMD18	TSSOP6	plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	SOT363

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PUMD18	T5%

[1] % = placeholder for manufacturing site code

8. Limiting values

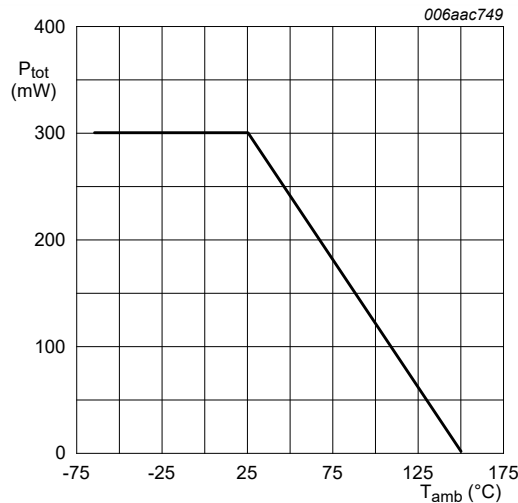
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transistor						
V_{CBO}	collector-base voltage	open emitter	[1]	-	50	V
V_{CEO}	collector-emitter voltage	open base	[1]	-	50	V
V_{EBO}	emitter-base voltage	open collector	[1]	-	7	V
V_I	input voltage	TR1		-7	20	V
		TR2		-20	7	V
I_O	output current		[1]	-	100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$	[2]	-	200	mW
Per device						
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$	[2]	-	300	mW
T_j	junction temperature			-	150	°C
T_{amb}	ambient temperature			-65	150	°C
T_{stg}	storage temperature			-65	150	°C

[1] For the PNP transistor with negative polarity.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



FR4 PCB, single-sided, 35 μm copper, tin-plated and standard footprint

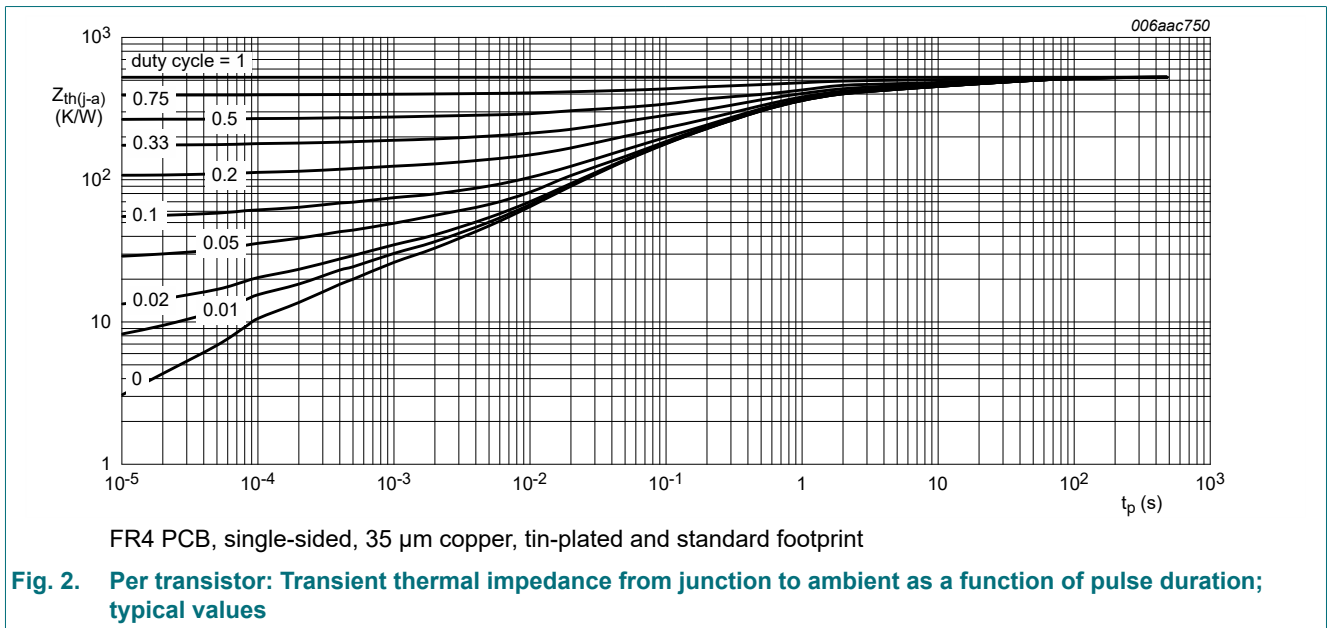
Fig. 1. Per device: Power derating curve

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	625	K/W
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	417	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



10. Characteristics

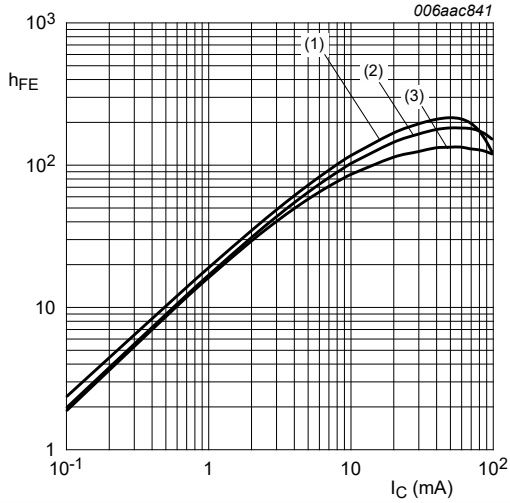
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per transistor							
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_C = 100 \mu\text{A}$; $I_E = 0 \text{ A}$; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	[1]	50	-	-	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	$I_C = 2 \text{ mA}$; $I_B = 0 \text{ A}$; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	[1]	50	-	-	V
I_{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}$; $I_E = 0 \text{ A}$; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	[1]	-	-	100	nA
I_{CEO}	collector-emitter cut-off current	$V_{CE} = 30 \text{ V}$; $I_B = 0 \text{ A}$; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	[1]	-	-	100	nA
		$V_{CE} = 30 \text{ V}$; $I_B = 0 \text{ A}$; $T_j = 150 \text{ }^\circ\text{C}$	[1]	-	-	5	μA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}$; $I_C = 0 \text{ A}$; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	[1]	-	-	600	μA
h_{FE}	DC current gain	$V_{CE} = 5 \text{ V}$; $I_C = 10 \text{ mA}$; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	[1]	50	-	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}$; $I_B = 0.5 \text{ mA}$; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	[1]	-	-	100	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5 \text{ V}$; $I_C = 100 \mu\text{A}$; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	[1]	-	0.9	0.3	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = 0.3 \text{ V}$; $I_C = 20 \text{ mA}$; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	[1]	2.5	1.5	-	V
R1	bias resistor 1 (input)		[2]	3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		[2]	1.7	2.1	2.6	
TR1 (NPN)							
C_c	collector capacitance	$V_{CB} = 10 \text{ V}$; $I_E = 0 \text{ A}$; $i_e = 0 \text{ A}$; $f = 1 \text{ MHz}$; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$		-	-	2.5	pF
f_T	transition frequency	$V_{CE} = 5 \text{ V}$; $I_C = 10 \text{ mA}$; $f = 100 \text{ MHz}$; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	[3]	-	230	-	MHz
TR2 (PNP)							
C_c	collector capacitance	$V_{CB} = -10 \text{ V}$; $I_E = 0 \text{ A}$; $i_e = 0 \text{ A}$; $f = 1 \text{ MHz}$; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$		-	-	3	pF
f_T	transition frequency	$V_{CE} = -5 \text{ V}$; $I_C = -10 \text{ mA}$; $f = 100 \text{ MHz}$; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	[3]	-	180	-	MHz

[1] For the PNP transistor with negative polarity.

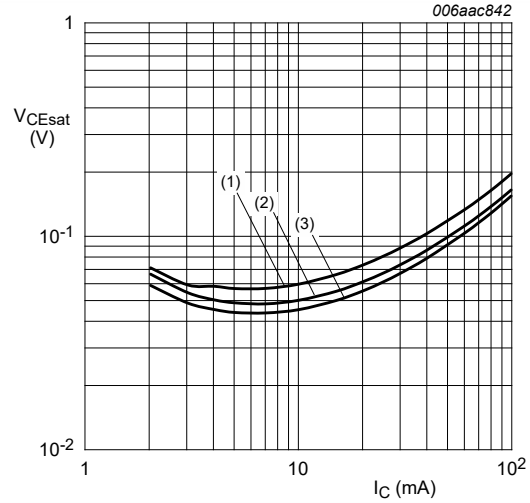
[2] See section "Test information" for resistor calculation and test conditions.

[3] Characteristics of built-in transistor



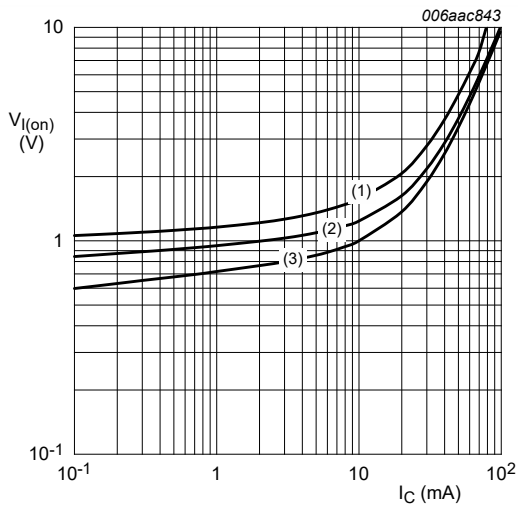
$V_{CE} = 5\text{ V}$
 (1) $T_{amb} = 100\text{ }^{\circ}\text{C}$
 (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 (3) $T_{amb} = -40\text{ }^{\circ}\text{C}$

Fig. 3. TR1 (NPN): DC current gain as a function of collector current; typical values



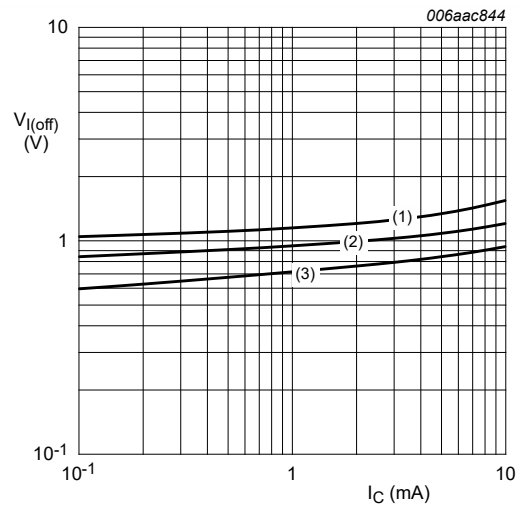
$I_C/I_B = 20$
 (1) $T_{amb} = 100\text{ }^{\circ}\text{C}$
 (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 (3) $T_{amb} = -40\text{ }^{\circ}\text{C}$

Fig. 4. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



$V_{CE} = 0.3\text{ V}$
 (1) $T_{amb} = -40\text{ }^{\circ}\text{C}$
 (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 (3) $T_{amb} = 100\text{ }^{\circ}\text{C}$

Fig. 5. TR1 (NPN): On-state input voltage as a function of collector current; typical values



$V_{CE} = 5\text{ V}$
 (1) $T_{amb} = -40\text{ }^{\circ}\text{C}$
 (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 (3) $T_{amb} = 100\text{ }^{\circ}\text{C}$

Fig. 6. TR1 (NPN): Off-state input voltage as a function of collector current; typical values

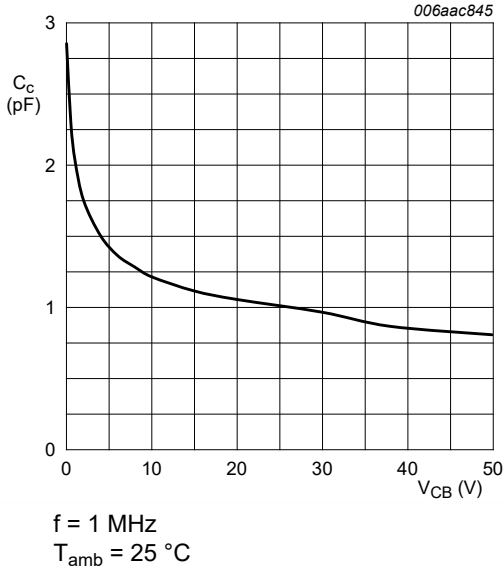


Fig. 7. TR1 (NPN): Collector capacitance as a function of collector-base voltage; typical values

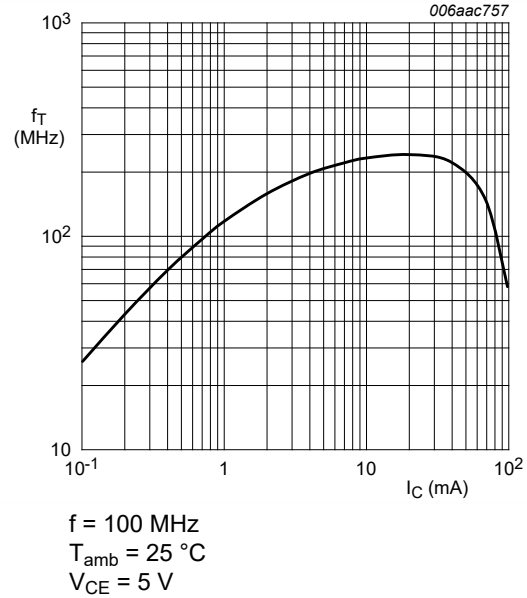


Fig. 8. TR1 (NPN): Transition frequency as a function of collector current; typical values of built-in transistor

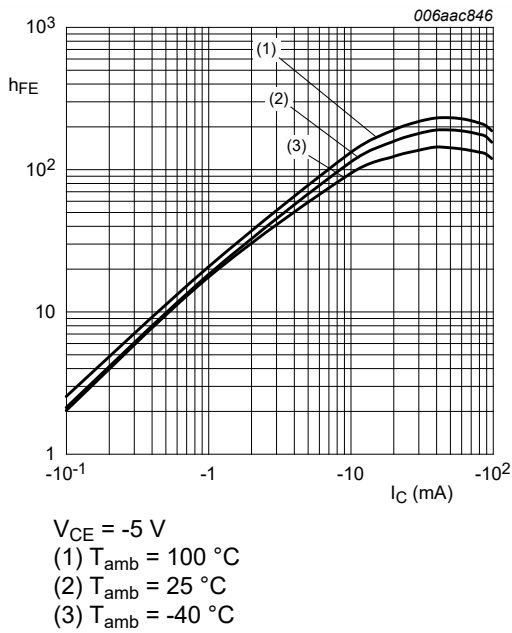


Fig. 9. TR2 (PNP): DC current gain as a function of collector current; typical values

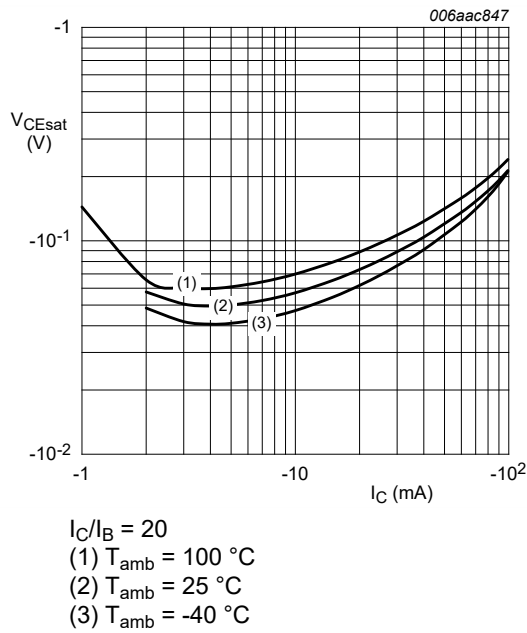
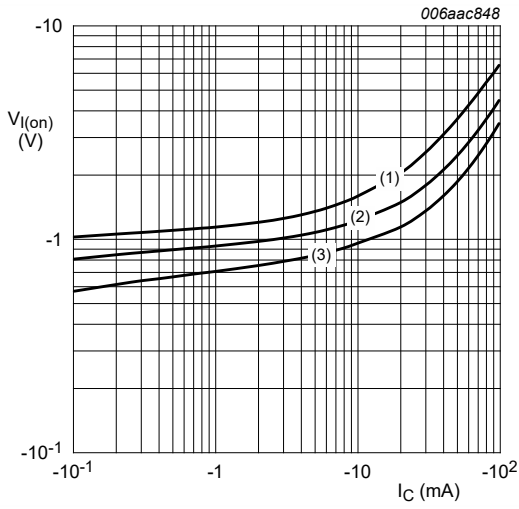
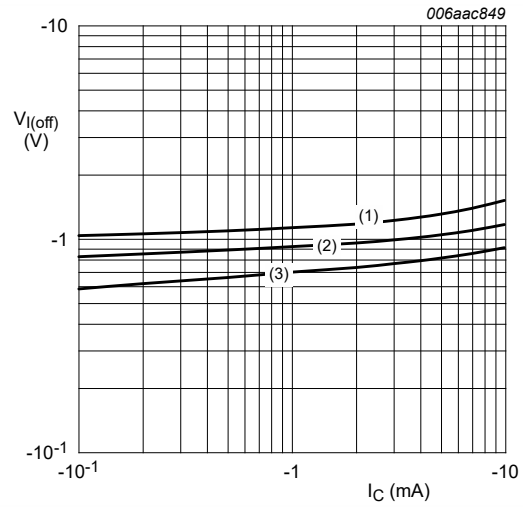


Fig. 10. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values



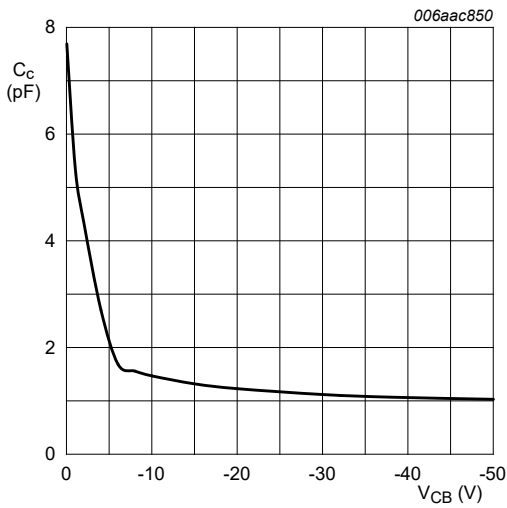
$V_{CE} = -0.3 \text{ V}$
 (1) $T_{amb} = -40 \text{ }^\circ\text{C}$
 (2) $T_{amb} = 25 \text{ }^\circ\text{C}$
 (3) $T_{amb} = 100 \text{ }^\circ\text{C}$

Fig. 11. TR2 (PNP): On-state input voltage as a function of collector current; typical values



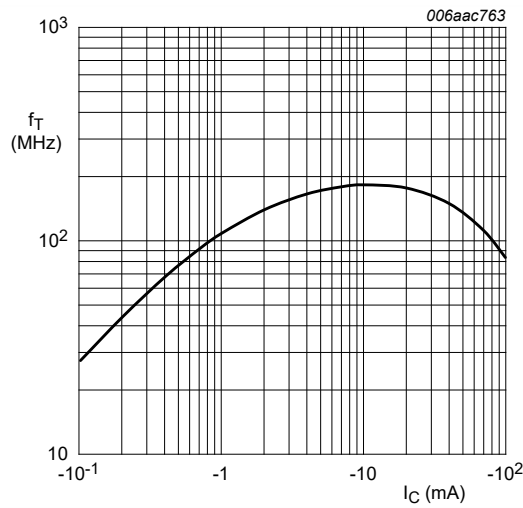
$V_{CE} = -5 \text{ V}$
 (1) $T_{amb} = -40 \text{ }^\circ\text{C}$
 (2) $T_{amb} = 25 \text{ }^\circ\text{C}$
 (3) $T_{amb} = 100 \text{ }^\circ\text{C}$

Fig. 12. TR2 (PNP): Off-state input voltage as a function of collector current; typical values



$f = 1 \text{ MHz}$
 $T_{amb} = 25 \text{ }^\circ\text{C}$

Fig. 13. TR2 (PNP): Collector capacitance as a function of collector-base voltage; typical values



$f = 100 \text{ MHz}$
 $T_{amb} = 25 \text{ }^\circ\text{C}$
 $V_{CE} = -5 \text{ V}$

Fig. 14. TR2 (PNP): Transition frequency as a function of collector current; typical values of built-in transistor

11. Test information

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

Resistor calculation

- Calculation of bias resistor 1 (R1)

$$R_1 = \frac{V(I_2) - V(I_1)}{I_2 - I_1}$$

- Calculation of bias resistor ratio (R2/R1)

$$\frac{R_2}{R_1} = \frac{V(I_4) - V(I_3)}{R_1 \cdot (I_4 - I_3)} - 1$$

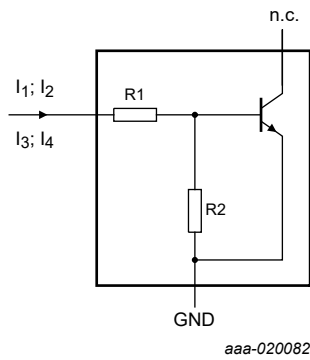


Fig. 15. NPN transistor: Resistor test circuit

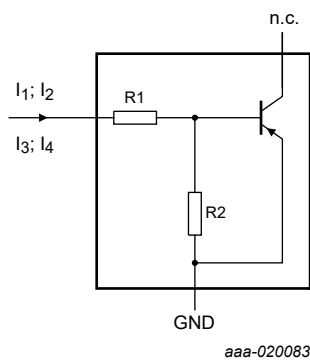


Fig. 16. PNP transistor: Resistor test circuit

Resistor test conditions

Table 8. Resistor test conditions

PUMD18	R1 (kΩ)	R2 (kΩ)	Test conditions			
			I ₁	I ₂	I ₃	I ₄
TR1 (NPN)	4.7	10	350 μA	450 μA	-350 μA	-450 μA
TR2 (PNP)	4.7	10	-350 μA	-450 μA	350 μA	450 μA

12. Package outline

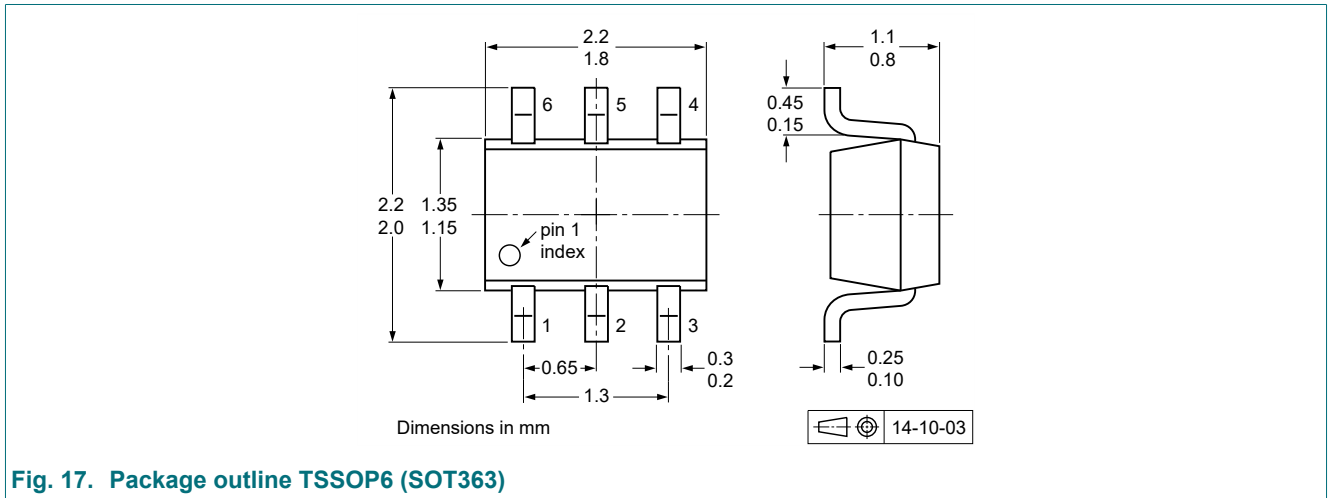


Fig. 17. Package outline TSSOP6 (SOT363)

13. Soldering

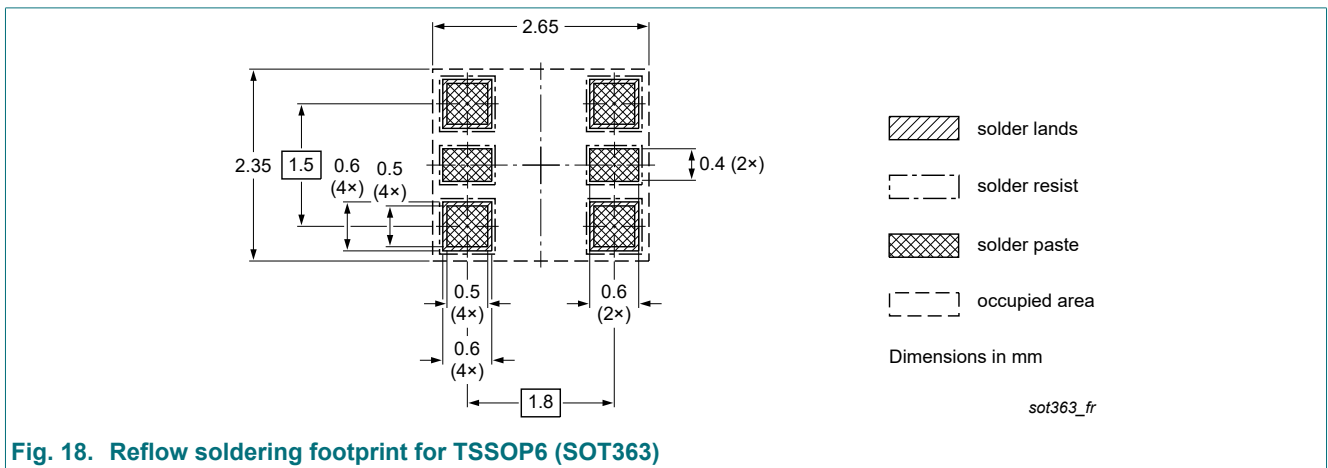


Fig. 18. Reflow soldering footprint for TSSOP6 (SOT363)

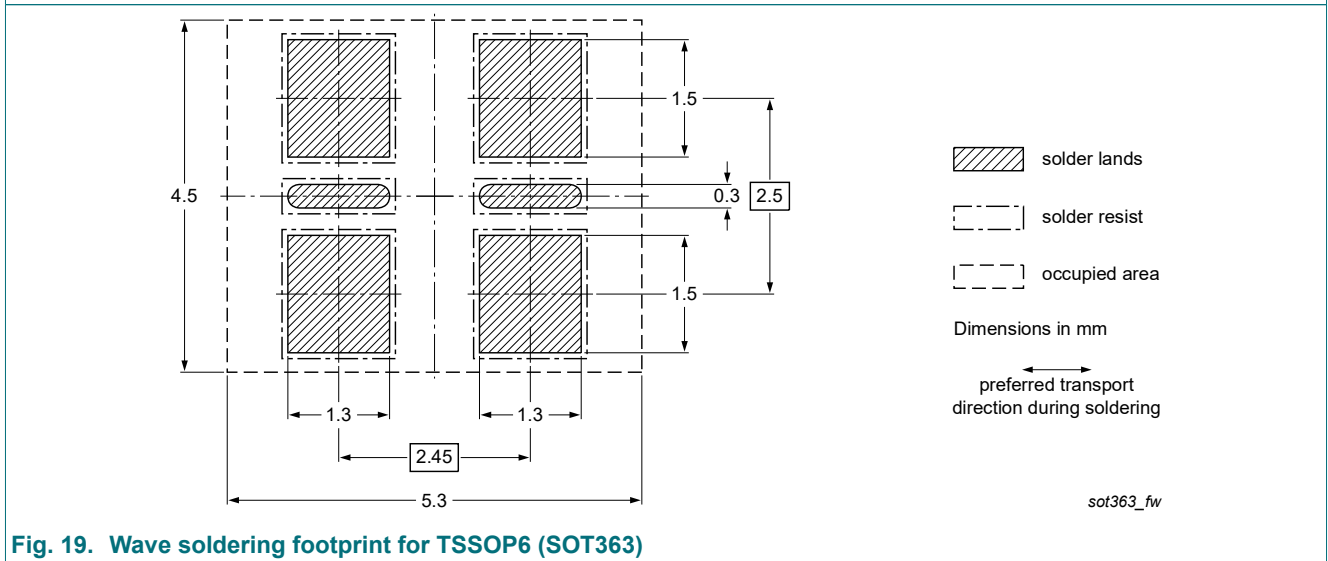


Fig. 19. Wave soldering footprint for TSSOP6 (SOT363)

14. Revision history

Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PUMD18 v.3	20230512	Product data sheet	-	PUMD18_PEMD18 v.2
Modifications:	<ul style="list-style-type: none"> The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. Family data sheet reduced to single type data sheet. Packing information removed. 			
PUMD18_PEMD18 v.2	20111221	Product data sheet	-	PUMD18 v.1
PUMD18 v.1	20050605	Product data sheet	-	-

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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